

### **SS8050**

# **2W Output Amplifier of Portable Radios in Class B Push-pull Operation.**

- Complimentary to SS8550
- Collector Current: I<sub>C</sub>=1.5A
- Collector Power Dissipation: P<sub>C</sub>=2W (T<sub>C</sub>=25°C)



## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

| Symbol           | Parameter                   | Ratings   | Units |
|------------------|-----------------------------|-----------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage      | 40        | V     |
| V <sub>CEO</sub> | Collector-Emitter Voltage   | 25        | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage        | 6         | V     |
| I <sub>C</sub>   | Collector Current           | 1.5       | Α     |
| P <sub>C</sub>   | Collector Power Dissipation | 1         | W     |
| T <sub>J</sub>   | Junction Temperature        | 150       | °C    |
| T <sub>STG</sub> | Storage Temperature         | -65 ~ 150 | °C    |

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

| Symbol   | Parameter                            | Test Condition   | Min.           | Тур.              | Max. | Units |
|--|--------------------------------------|--|----------------|-------------------|------|-------|
| BV <sub>CBO</sub>  | Collector-Base Breakdown Voltage     | $I_{C}=100\mu A, I_{E}=0$  | 40             |                   |      | V     |
| BV <sub>CEO</sub>  | Collector-Emitter Breakdown Voltage  | $I_C=2mA$ , $I_B=0$  | 25             |                   |      | V     |
| BV <sub>EBO</sub>  | Emitter-Base Breakdown Voltage       | I <sub>E</sub> =100μA, I <sub>C</sub> =0                                 | 6              |                   |      | V     |
| I <sub>CBO</sub>   | Collector Cut-off Current            | $V_{CB}$ =35V, $I_E$ =0  |                |                   | 100  | nA    |
| I <sub>EBO</sub>   | Emitter Cut-off Current              | $V_{EB}=6V, I_{C}=0$   |                |                   | 100  | nA    |
| h <sub>FE1</sub><br>h <sub>FE2</sub><br>h <sub>FE3</sub> | DC Current Gain                      | $V_{CE}=1V, I_{C}=5mA$ $V_{CE}=1V, I_{C}=100mA$ $V_{CE}=1V, I_{C}=800mA$ | 45<br>85<br>40 | 135<br>160<br>110 | 300  |       |
| V <sub>CE</sub> (sat)                                    | Collector-Emitter Saturation Voltage | I <sub>C</sub> =800mA, I <sub>B</sub> =80mA                              |                | 0.28              | 0.5  | V     |
| V <sub>BE</sub> (sat)                                    | Base-Emitter Saturation Voltage      | I <sub>C</sub> =800mA, I <sub>B</sub> =80mA                              |                | 0.98              | 1.2  | V     |
| V <sub>BE</sub> (on)                                     | Base-Emitter On Voltage              | V <sub>CE</sub> =1V, I <sub>C</sub> =10mA                                |                | 0.66              | 1    | V     |
| C <sub>ob</sub>  | Output Capacitance                   | V <sub>CB</sub> =10V, I <sub>E</sub> =0<br>f=1MHz                        |                | 9.0               |      | pF    |
| f <sub>T</sub>   | Current Gain Bandwidth Product       | V <sub>CE</sub> =10V, I <sub>C</sub> =50mA                               | 100            | 190               |      | MHz   |

## **h**<sub>FE</sub> Classification

| Classification   | В        | С         | D         |
|------------------|----------|-----------|-----------|
| h <sub>FE2</sub> | 85 ~ 160 | 120 ~ 200 | 160 ~ 300 |

## **Typical Characteristics**

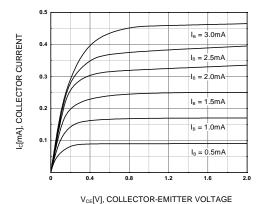


Figure 1. Static Characteristic

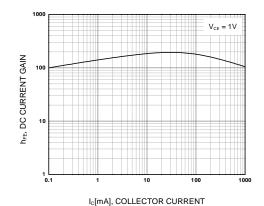


Figure 2. DC current Gain

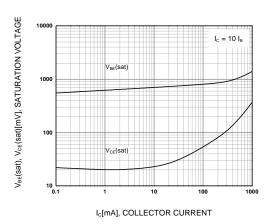


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

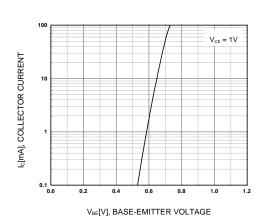


Figure 4. Base-Emitter On Voltage

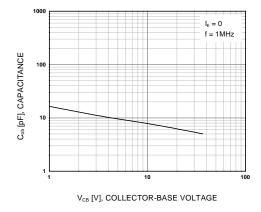


Figure 5. Collector Output Capacitance

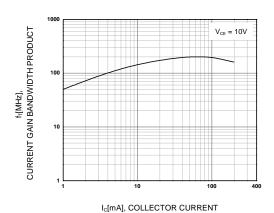
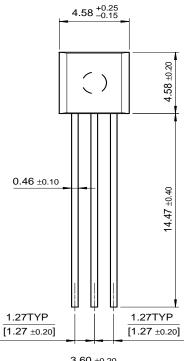


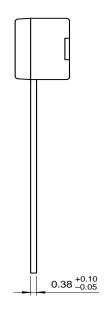
Figure 6. Current Gain Bandwidth Product

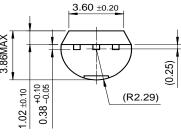
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## **Package Demensions**

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| CROSSVOLT™           | GlobalOptoisolator™ | Power247™                | SuperSOT™-6           |
| DenseTrench™         | GTO™                | PowerTrench <sup>®</sup> | SuperSOT™-8           |
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| EcoSPARK™            | ISOPLANAR™          | QS™                      | TruTranslation™       |
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